



PSMN2R8-40PS

N-channel TO220 40 V 2.8 mΩ standard level MOSFET

11 February 2013

Product data sheet

1. General description

Standard level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

3. Applications

- DC-to-DC converters
- Load switching
- Motor control
- Server power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; Fig. 1	[1]	-	-	100	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; Fig. 2		-	-	211	W
T _j	junction temperature			-55	-	175	°C
Static characteristics							
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 100 °C; Fig. 12 ; Fig. 13		-	-	4.5	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 13	[2]	-	2.3	2.8	mΩ
Dynamic characteristics							
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 25 A; V _{DS} = 20 V; Fig. 14 ; Fig. 15		-	17	-	nC
Q _{G(tot)}	total gate charge			-	71	-	nC



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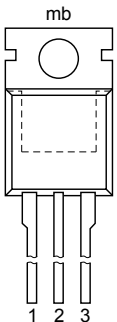
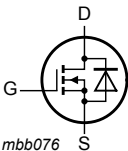
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ °C}$; $I_D = 100\text{ A}$; $V_{sup} \leq 40\text{ V}$; unclamped; $R_{GS} = 50\text{ }\Omega$	-	-	407	mJ

[1] Continuous current rating is limited by package.

[2] Measured 3 mm from package.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 TO-220AB (SOT78)	 <i>mbb076</i>
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN2R8-40PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN2R8-40PS	PSMN2R8-40PS

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ }^{\circ}\text{C}$; $T_j \leq 175\text{ }^{\circ}\text{C}$		-	40	V
V_{DGR}	drain-gate voltage	$T_j \geq 25\text{ }^{\circ}\text{C}$; $T_j \leq 175\text{ }^{\circ}\text{C}$; $R_{GS} = 20\text{ k}\Omega$		-	40	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 100\text{ }^{\circ}\text{C}$; Fig. 1	[1]	-	100	A
		$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ }^{\circ}\text{C}$; Fig. 1	[1]	-	100	A
I_{DM}	peak drain current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ }^{\circ}\text{C}$; Fig. 3		-	797	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ }^{\circ}\text{C}$; Fig. 2		-	211	W
T_{stg}	storage temperature			-55	175	$^{\circ}\text{C}$
T_j	junction temperature			-55	175	$^{\circ}\text{C}$
Source-drain diode						
I_S	source current	$T_{mb} = 25\text{ }^{\circ}\text{C}$		-	100	A
I_{SM}	peak source current	pulsed; $t_p \leq 10\text{ }\mu\text{s}$; $T_{mb} = 25\text{ }^{\circ}\text{C}$		-	797	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$; $I_D = 100\text{ A}$; $V_{sup} \leq 40\text{ V}$; unclamped; $R_{GS} = 50\text{ }\Omega$		-	407	mJ

[1] Continuous current rating is limited by package.

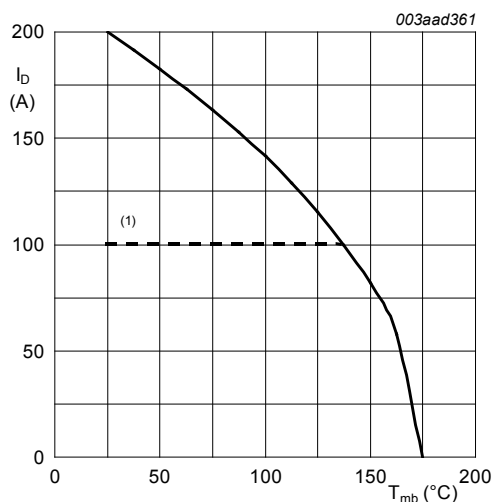


Fig. 1. Continuous drain current as a function of mounting base temperature

$$V_{GS} \geq 10\text{ V}$$

(1) Capped at 100 A due to package.

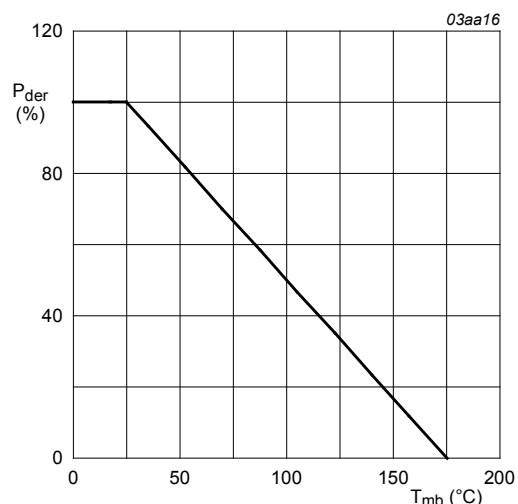


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100\%$$

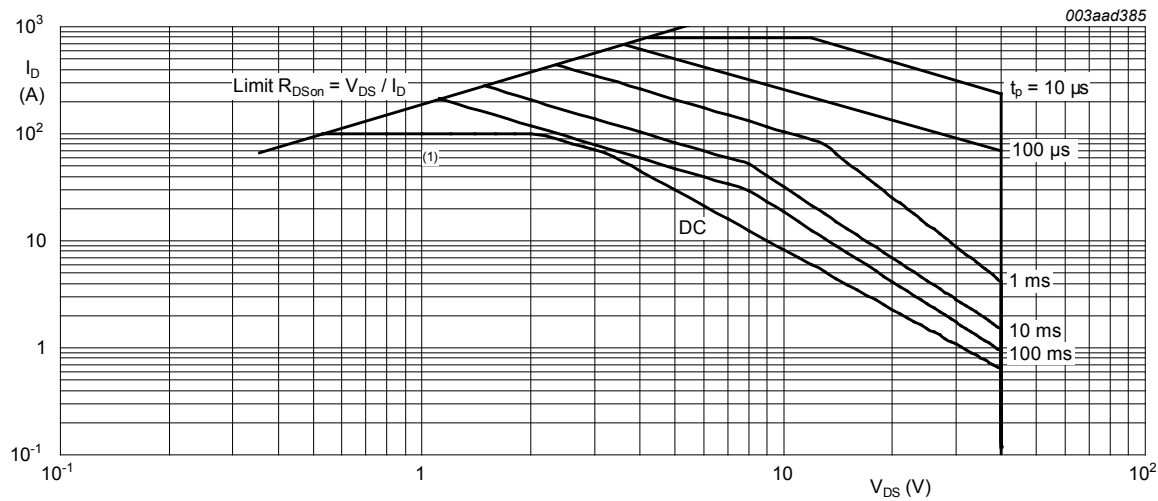


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25\text{ }^{\circ}\text{C}$; I_{DM} is a single pulse; (1) Capped at 100 A due to package

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 4	-	0.4	0.7	K/W

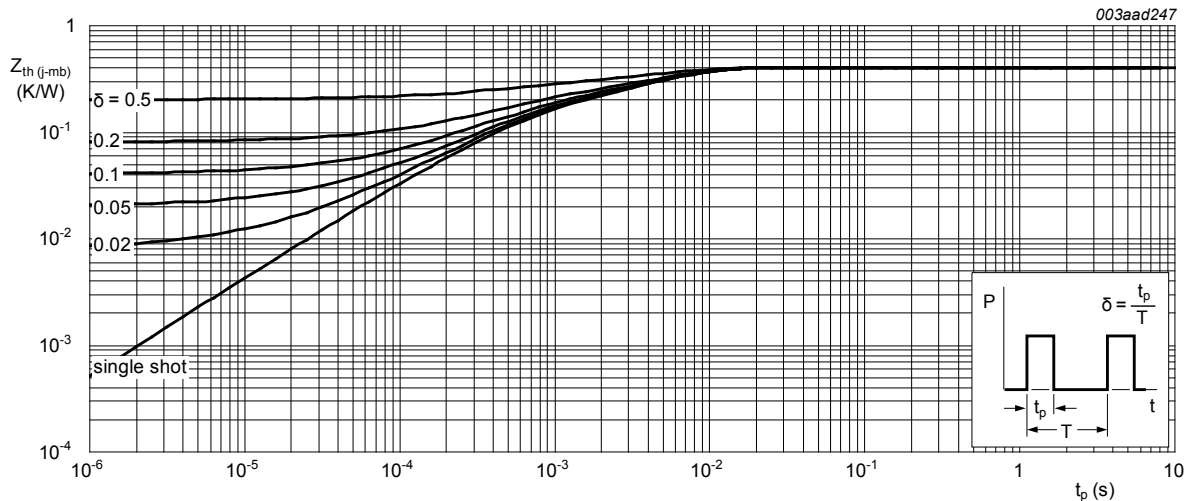


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

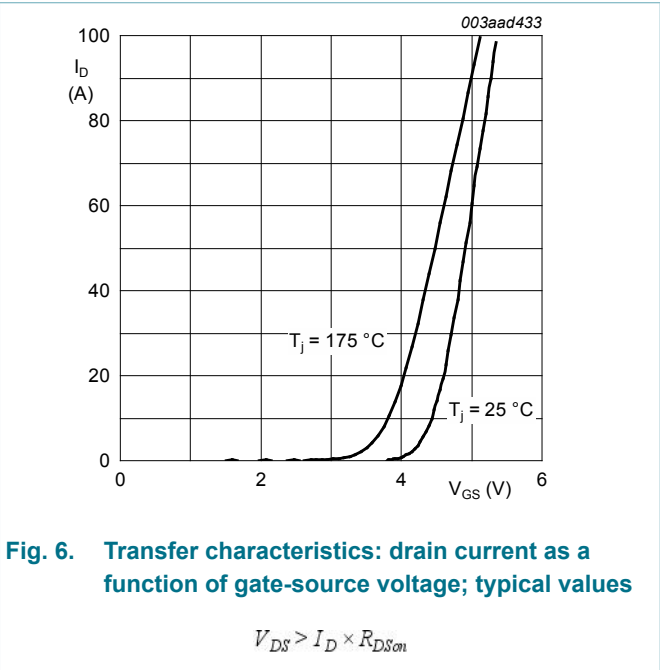
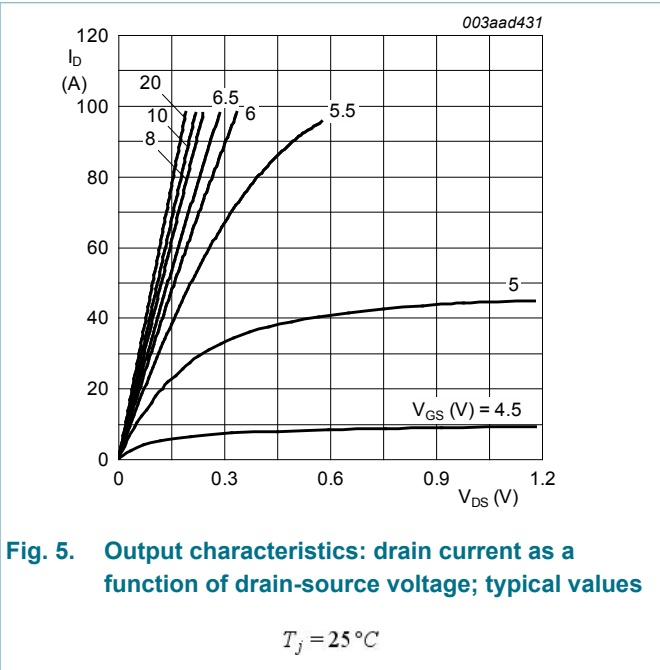
Table 7. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\ \mu\text{A}$; $V_{GS} = 0\ \text{V}$; $T_J = -55\ ^\circ\text{C}$		36	-	-	V
		$I_D = 250\ \mu\text{A}$; $V_{GS} = 0\ \text{V}$; $T_J = 25\ ^\circ\text{C}$		40	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\ \text{mA}$; $V_{DS} = V_{GS}$; $T_J = -55\ ^\circ\text{C}$; Fig. 10 ; Fig. 11		-	-	4.6	V
		$I_D = 1\ \text{mA}$; $V_{DS} = V_{GS}$; $T_J = 175\ ^\circ\text{C}$; Fig. 10 ; Fig. 11		1	-	-	V
		$I_D = 1\ \text{mA}$; $V_{DS} = V_{GS}$; $T_J = 25\ ^\circ\text{C}$; Fig. 10 ; Fig. 11		2.3	3	4	V
I_{DSS}	drain leakage current	$V_{DS} = 40\ \text{V}$; $V_{GS} = 0\ \text{V}$; $T_J = 25\ ^\circ\text{C}$		-	0.3	10	μA
		$V_{DS} = 40\ \text{V}$; $V_{GS} = 0\ \text{V}$; $T_J = 125\ ^\circ\text{C}$		-	-	150	μA
I_{GSS}	gate leakage current	$V_{GS} = 20\ \text{V}$; $V_{DS} = 0\ \text{V}$; $T_J = 25\ ^\circ\text{C}$		-	10	100	nA
		$V_{GS} = -20\ \text{V}$; $V_{DS} = 0\ \text{V}$; $T_J = 25\ ^\circ\text{C}$		-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\ \text{V}$; $I_D = 10\ \text{A}$; $T_J = 100\ ^\circ\text{C}$; Fig. 12 ; Fig. 13		-	-	4.5	mΩ
		$V_{GS} = 10\ \text{V}$; $I_D = 10\ \text{A}$; $T_J = 175\ ^\circ\text{C}$; Fig. 12 ; Fig. 13		-	-	5.6	mΩ
		$V_{GS} = 10\ \text{V}$; $I_D = 10\ \text{A}$; $T_J = 25\ ^\circ\text{C}$; Fig. 13	[1]	-	2.3	2.8	mΩ
R_G	internal gate resistance (AC)	$f = 1\ \text{MHz}$		-	0.7	-	Ω
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	$I_D = 0\ \text{A}$; $V_{DS} = 0\ \text{V}$; $V_{GS} = 10\ \text{V}$		-	61	-	nC
		$I_D = 25\ \text{A}$; $V_{DS} = 20\ \text{V}$; $V_{GS} = 10\ \text{V}$; Fig. 14 ; Fig. 15		-	71	-	nC
Q_{GS}	gate-source charge			-	21	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge			-	13	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge			-	8.5	-	nC
Q_{GD}	gate-drain charge			-	17	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25\ \text{A}$; $V_{DS} = 20\ \text{V}$; Fig. 14 ; Fig. 15		-	4.7	-	V
C_{iss}	input capacitance	$V_{DS} = 20\ \text{V}$; $V_{GS} = 0\ \text{V}$; $f = 1\ \text{MHz}$;		-	4491	-	pF
C_{oss}	output capacitance	$T_J = 25\ ^\circ\text{C}$; Fig. 16		-	937	-	pF

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
C _{rss}	reverse transfer capacitance			-	464	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 20 V; R _L = 0.8 Ω; V _{GS} = 10 V; R _{G(ext)} = 4.7 Ω		-	28	-	ns
t _r	rise time			-	29	-	ns
t _{d(off)}	turn-off delay time			-	52	-	ns
t _f	fall time			-	23	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I _S = 10 A; V _{GS} = 0 V; T _j = 25 °C; Fig. 17		-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 40 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V; V _{DS} = 20 V		-	47	-	ns
Q _r	recovered charge	I _S = 40 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V; V _{DS} = 20 V; T _j = 25 °C		-	61	-	nC

[1] Measured 3 mm from package.



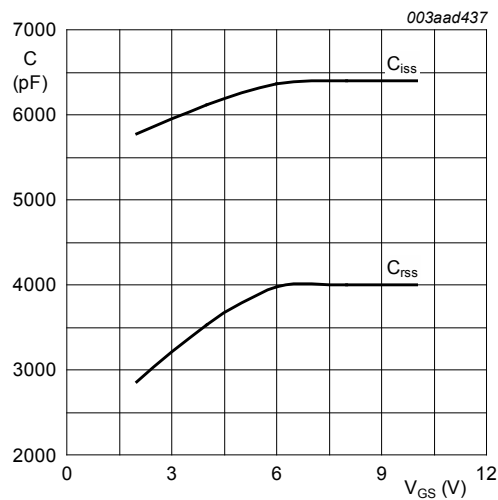


Fig. 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

$V_{DS} = 0\text{ V}; f = 1\text{ MHz}$

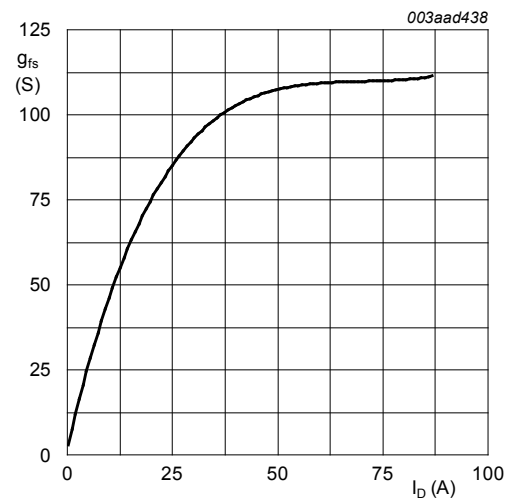


Fig. 8. Forward transconductance as a function of drain current; typical values

$T_j = 25^\circ\text{C}; V_{DS} = 15\text{ V}$

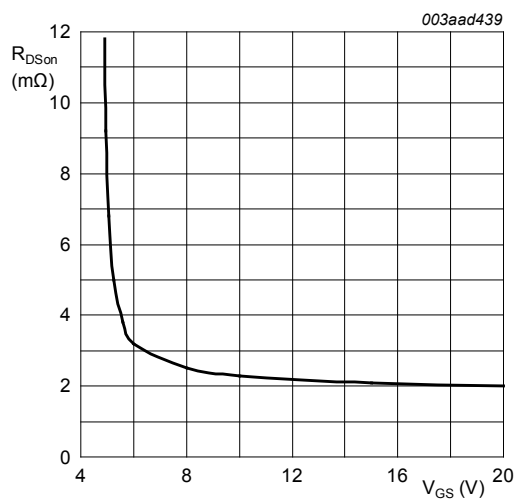


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25^\circ\text{C}; I_D = 25\text{ A}$

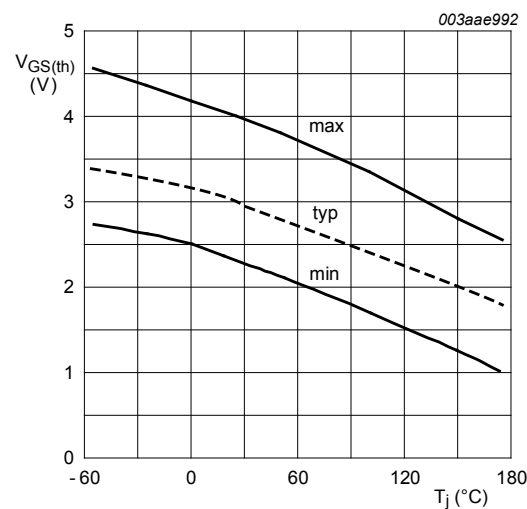


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

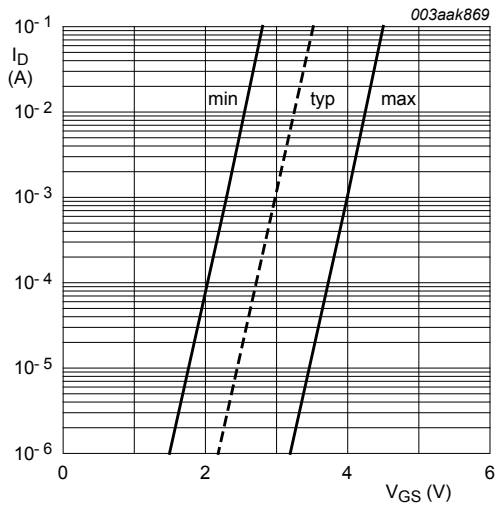


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25\text{ }^{\circ}\text{C}; V_{DS} = 5\text{ V}$$

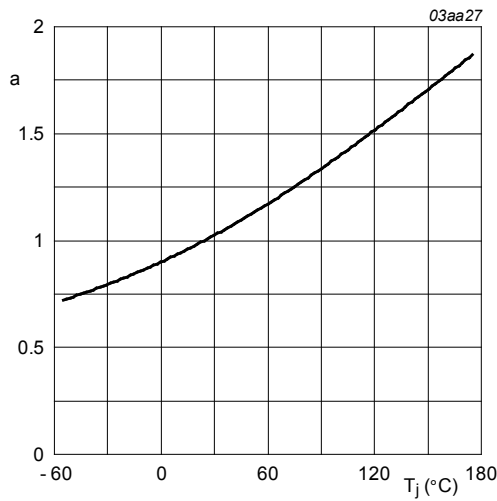


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}\text{C})}}$$

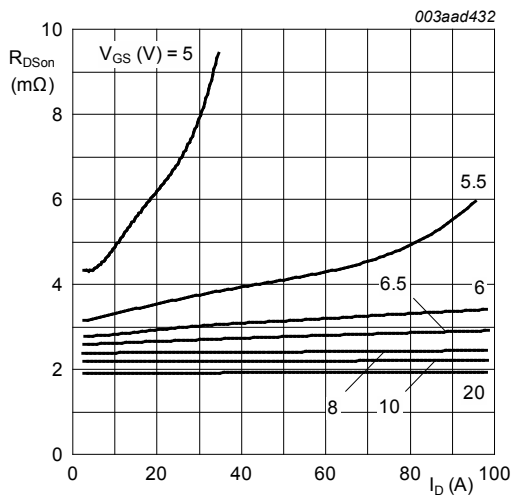


Fig. 13. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25\text{ }^{\circ}\text{C}$$

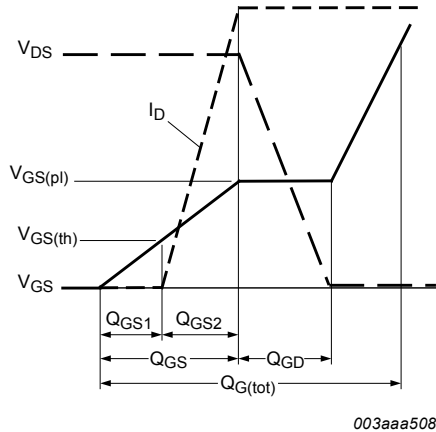


Fig. 14. Gate charge waveform definitions

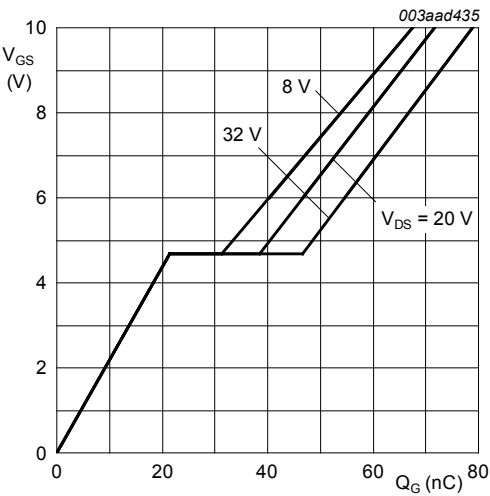


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$T_j = 25\text{ }^{\circ}\text{C}; I_D = 10\text{ A}$

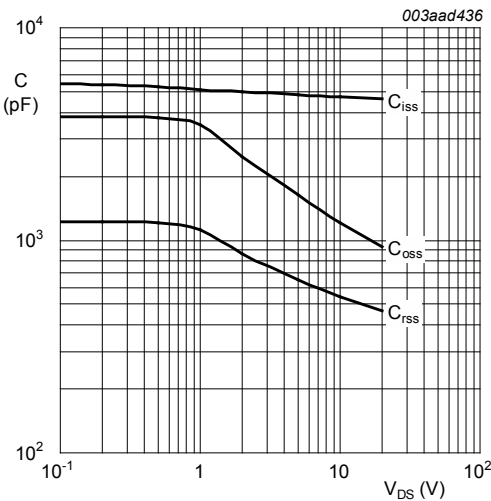


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$

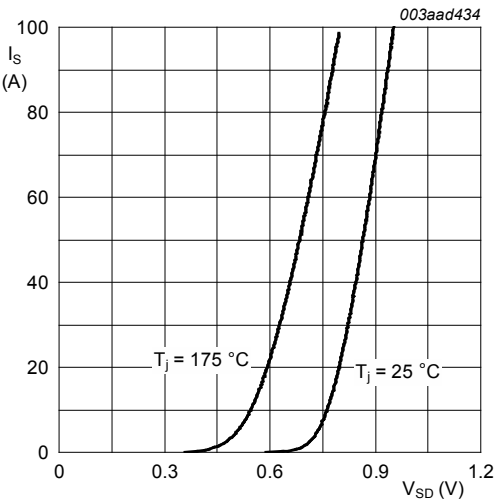


Fig. 17. Source current as a function of source-drain voltage; typical values

$V_{GS} = 0\text{ V}$

11. Package outline

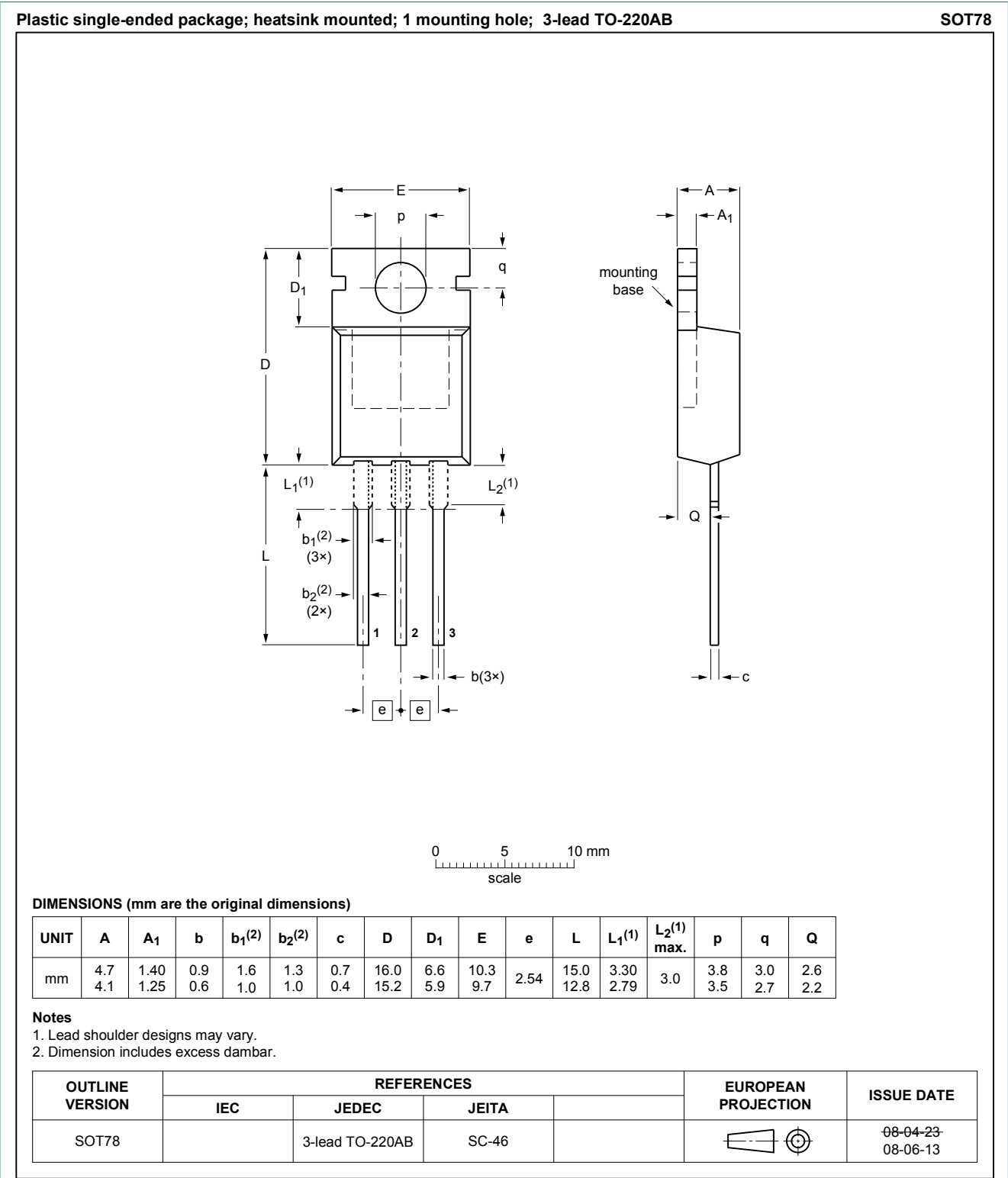


Fig. 18. Package outline TO-220AB (SOT78)

12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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